

Attorney's Docket No.: 07043-060002
 Client's Ref. No.: B97-063-2

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JUN 17 2005

Number of pages including this page 3

Applicant : Brosnihan et al

Art Unit : 2814

Serial No. : 09/342,348

Examiner : Anh D. Mai

Filed : June 29, 1999

Title : METHOD OF FABRICATING A MICROFABRICATED HIGH ASPECT RATIO DEVICE WITH ELECTRICAL ISOLATION

MAIL STOP AMENDMENT

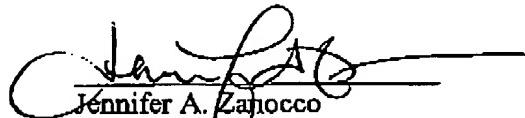
Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Attached to this facsimile communication cover sheet is Reply to Examiner Interview Summary mailed June 2, 2005, faxed this 17th day of June, 2005, to the United States Patent and Trademark Office.

Respectfully submitted,



Jennifer A. Zanocco
 Reg. No. 54,563

Date: June 17, 2005

Customer No. 26181
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Mail Stop Amendment
 Commissioner for Patents
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REPLY TO INTERVIEW SUMMARY OF JUNE 2, 2005

In reply to the Interview Summary of June 2, 2005, the Applicants submit the following remarks.

The Applicants discussed amending claim 1 to include a step of etching a first trench in single crystal silicon, a step of depositing a dielectric isolation layer in the first trench and a step of etching a second trench in the single crystal silicon, the etching of the second trench to be performed after depositing the dielectric isolation layer. Bashir etches two trenches 120, 121 simultaneously in a silicon layer 106. Bashir does not perform two separate etching steps in the silicon layer 106.

In the Interview Summary, the Examiner states that the "Applicants will amend the claim to distinguish from the reference namely the two trenches will be formed at the different process steps."

Applicants do not admit that this amendment was required to distinguish the claims from U.S. Patent No. 5,747,353 ("Bashir"). The Applicants have provided, in previous written communications with the Examiner, reasons that Bashir does not disclose at least one of the limitations required by claim 1. The amendment was made to further prosecution.

CERTIFICATE OF TRANSMISSION BY FACSIMILE

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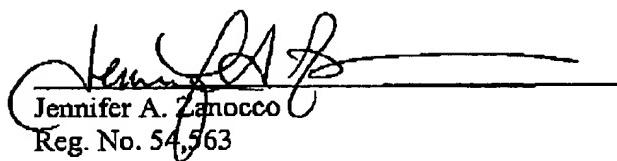
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Page : 2 of 2

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